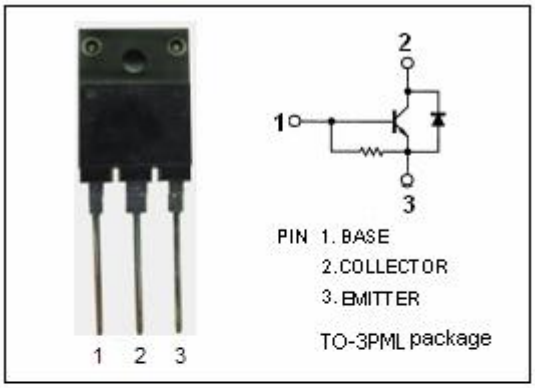
isc Silicon NPN Power Transistor — 2SD2300

DESCRIPTION

- High Breakdown Voltage-
  : V_{CBO}= 1500V (Min)
- Built-in Damper Diode
- Minimum Lot-to-Lot variations for robust device performance and reliable operation
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

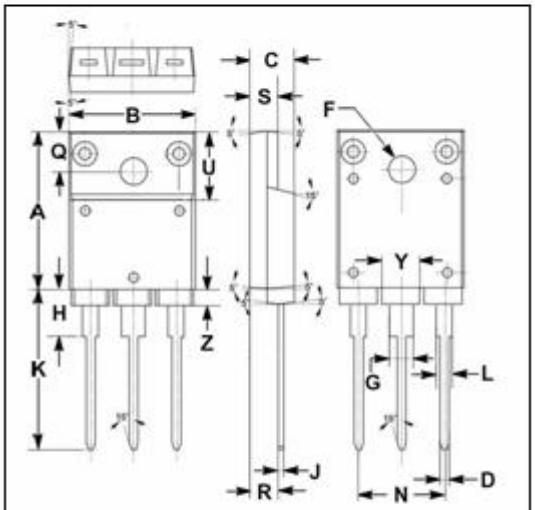


APPLICATIONS

- Designed for CTV horizontal deflection output applications

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CES}	Collector-Emitter Voltage	1500	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current- Continuous	5	A
$I_{C(peak)}$	Collector Current-Peak	6	A
$I_{C(surge)}$	Collector Current-Surge	16	A
P_C	Collector Power Dissipation @ T_C=25℃	50	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm MIN	MAX
A	19.90	20.10
B	15.75	16.10
C	5.50	5.70
D	0.90	1.10
F	3.30	3.50
G	2.90	3.20
H	5.90	6.10
J	0.595	0.70
K	21.10	22.50
L	1.90	2.25
N	10.80	11.00
Q	4.90	5.10
R	3.75	3.95
S	3.20	3.60
U	9.90	10.10
Y	4.20	4.90
Z	1.90	2.10

isc Silicon NPN Power Transistor 2SD2300

ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= 200mA; I_C= 0	6			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 4.5A; I_B= 1.2A			5.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 4.5A; I_B= 1.2A			1.5	V
I_{CES}	Collector Cutoff Current	V_{CE}= 1500V; R_{BE}= 0			0.5	mA
h_{FE}	DC Current Gain	I_C= 1A; V_{CE}= 5V			20	
V_{ECF}	C-E Diode Forward Voltage	I_F= 6A			3.0	V
t_f	Fall Time	I_C= 4A; I_{B1}= 0.8A; I_{B2}≈ -1.5A			1.0	μs